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PATENT

28116 / IDS  
Lemus  
3/14/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

ASHRAF W. LOTFI, et al.

Serial No.: 09/448,856

Filed: November 23, 1999

For: SiC NMOSFET FOR USE AS A POWER SWITCH  
AND A METHOD OF MANUFACTURING THE SAME

Group No.: 2811

Examiner: O. Nadav

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Commissioner of Patents  
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Sir:

CERTIFICATION FOR INFORMATION DISCLOSURE STATEMENT  
(37 C.F.R. § 1.97(e))

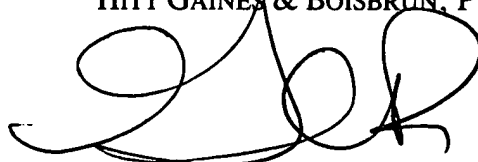
This certification is being made for the Information Disclosure Statement accompanying this certification.

I hereby certify that each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the statement.

As attorney for the Applicant, I am signing below on the basis of the information supplied  
by an individual designated in § 1.56(c).

Respectfully submitted,

HITT GAINES & BOISBRUN, P.C.

A handwritten signature in black ink, appearing to read 'G. Boisbrun', written over a horizontal line.

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